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L1: (9) "6061228"

L2: (3) "6351880"

L3: (2613025) via\$1

L4: (535) embedded near capacitor

L5: (282) 3 and 4

L6: (191) 5 and fill\$

L7: (14) 6 and LTCC

L8: (20446) bore adj hole

L9: (2) 8 near capacitor

L10: (68) on adj chip

L11: (26371) on-chip

L12: (298) 11 near capacitor

L13: (26) 12 and hole

L14: (0) 12 and LTCC

L15: (150) 12 and via\$1

L16: (7) capacitor adj using adj via\$1

L17: (594042) capacitor\$1

L18: (17737) 3 near 17

L19: (15109) 3 adj 17

L20: (443) 19 and embedded

L21: (70) 20 and IC

L22: (172) 20 and chip

L23: (13501) via\$1 adj capacitor

L24: (23) 4 and 23

L25: (2153) metallic near via\$1

L27: (313) 25 and 17

L28: (164) 27 and chip

L29: (0) capacitor adj formed adj from adj via\$

L30: (7) 25 and capacitor and LTCC

L31: (0) metallic near via\$1 near capacitor

L32: (105605) 361/\$.cccls.

L33: (493) 23 and 32

L34: (5) 33 and LTCC

L35: (34) 33 and multilayer

USPAT: US-PG-PUB: EPO: JPO: DERWENT: ISM: TOR

33 and multilayer

16/27/04 TDW

US 200401842192004092338Assembly of semiconductor device, interposer and substrate361/306.3Otsuka, Jun et al.

US 200401746562004090920Window via capacitor361/306.3MacNeal, Jason et al.

US 200400666172004040820Circuit board device and its manufacturing method361/683Hirabayashi, Takayuki et al.

US 200400421552004030422Controlled ESR low inductance361/309Ritter, Andrew P. et al.

ReadyNUM

L Number	Hits	Search Text	DB	Time stamp
1	9	"6061228"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:33
2	3	"6351880"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:25
3	2613025	via\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:40
4	535	embedded near capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:41
5	282	via\$1 and (embedded near capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:42
6	191	(via\$1 and (embedded near capacitor)) and fill\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:42
7	14	((via\$1 and (embedded near capacitor)) and fill\$5) and LTCC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:45
8	20446	bore adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:46
9	2	(bore adj hole) near capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:47
10	68	on adj chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:47
11	26371	on-chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:48
12	298	on-chip near capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:48

13	26	(on-chip near capacitor) and hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:49
14	0	(on-chip near capacitor) and LTCC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:49
15	150	(on-chip near capacitor) and via\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:19
16	7	capacitor adj using adj via\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:22
17	594042	capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:23
18	17737	via\$1 near capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:24
19	15109	via\$1 adj capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:24
20	443	(via\$1 adj capacitor\$1) and embedded	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:25
21	70	((via\$1 adj capacitor\$1) and embedded) and IC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:40
22	172	((via\$1 adj capacitor\$1) and embedded) and chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:26
23	13501	via\$1 adj capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:40
24	23	(embedded near capacitor) and (via\$1 adj capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:11

25	2153	metallic near via\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:36
27	313	(metallic near via\$1) and capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:13
28	164	((metallic near via\$1) and capacitor\$1) and chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:13
29	0	capacitor adj formed adj from adj via\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:29
30	7	(metallic near via\$1) and capacitor and LTCC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:29
31	0	metallic near via\$1 near capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:37
32	105605	361/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:38
33	493	(via\$1 adj capacitor) and 361/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:38
34	5	((via\$1 adj capacitor) and 361/\$.ccls.) and LTCC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:42
35	34	((via\$1 adj capacitor) and 361/\$.ccls.) and multilayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:42